P-Channel NexFET™ Power MOSFETs

Check for Samples: CSD25401Q3

FEATURES

- **Ultra Low Q_g and Q_{gd}**
- **Low Thermal Resistance**
- **Low $R_{DS(on)}$**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- **SON 3.3mm x 3.3mm Plastic Package**

APPLICATIONS

- **DC-DC Converters**
- **Battery Management**
- **Load Switch**
- **Battery Protection**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion load management applications. The SON 3×3 package offers excellent thermal performance for the size of the package.

Top View

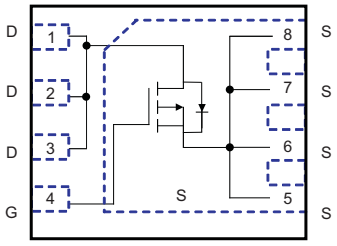


Table 1. PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	–20		V
Q_g	Gate Charge Total (4.5V)	8.8		nC
Q_{gd}	Gate Charge Gate to Drain	2.1		nC
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = –2.5V	13.5	mΩ
		V_{GS} = –4.5V	8.8	mΩ
V_{th}	Threshold Voltage	–0.85		V

ORDERING INFORMATION

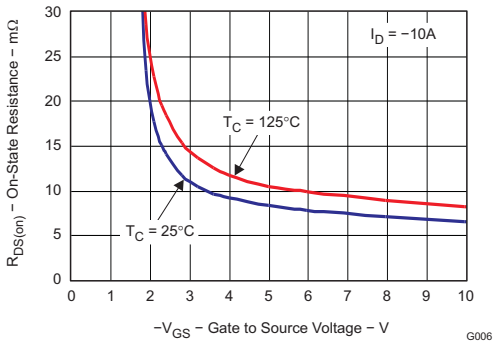
Device	Package	Media	Qty	Ship
CSD25401Q3	SON 3 × 3 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

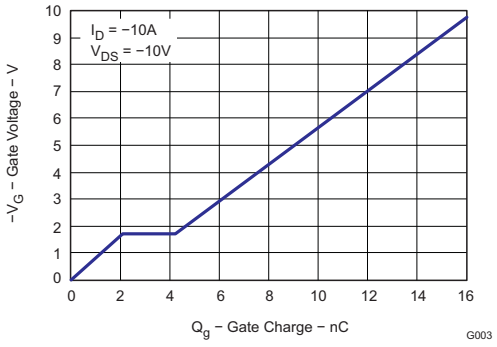
T_A = 25°C unless otherwise stated		VALUE	UNIT
V_{DS}	Drain to Source Voltage	–20	V
V_{GS}	Gate to Source Voltage	+12 / -12	V
I_D	Continuous Drain Current, T_C = 25°C	–60	A
	Continuous Drain Current(1)	–14	A
I_{DM}	Pulsed Drain Current, T_A = 25°C(2)	–82	A
P_D	Power Dissipation(1)	2.8	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	–55 to 150	°C

(1) $R_{\theta JA}$ = 45°C/W on 1inch^2 Cu (2 oz.) on 0.060" thick FR4 PCB.
(2) Pulse width ≤300µs , duty cycle ≤2%

$R_{DS(ON)}$ vs V_{GS}



Gate Charge



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ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Characteristics						
BV_{DSS}	Drain to Source Voltage	V_{GS} = 0V, I_D = –250µA	–20			V
I_{DSS}	Drain to Source Leakage Current	V_{GS} = 0V, V_{DS} = –20V to –16V			–1	µA
I_{GSS}	Gate to Source Leakage Current	V_{DS} = 0V, V_{GS} = ±12V			–100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{DS} = V_{GS}, I_D = –250µA	–0.6	–0.85	–1.2	V
$R_{DS(on)}$	Drain to Source On Resistance	V_{GS} = –2.5V, I_D = –10A		13.5	18.2	mΩ
		V_{GS} = –4.5V, I_D = –10A		8.8	11.7	mΩ
g_{fs}	Transconductance	V_{DS} = –15V, I_D = –10A		43		S
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V, V_{DS} = –10V, f = 1MHz		1070	1400	pF
C_{OSS}	Output Capacitance			560	730	pF
C_{RSS}	Reverse Transfer Capacitance			180	230	pF
Q_g	Gate Charge Total (4.5V)	V_{DS} = –10V, I_D = –10A		8.8	12.3	nC
Q_{gd}	Gate Charge Gate to Drain			2.1		nC
Q_{gs}	Gate Charge Gate to Source			2.1		nC
$Q_{g(th)}$	Gate Charge at Vth			0.9		nC
Q_{OSS}	Output Charge	V_{DS} = –10V, V_{GS} = 0V		8.2		nC
$t_{d(on)}$	Turn On Delay Time	V_{DS} = –10V, V_{GS} = –4.5V, I_D = –10A , R_G = 5.1Ω		8.1		ns
t_r	Rise Time			3.9		ns
$t_{d(off)}$	Turn Off Delay Time			13.5		ns
t_f	Fall Time			12.6		ns
Diode Characteristics						
V_{SD}	Diode Forward Voltage	I_S = –10A, V_{GS} = 0V		–0.7	–1	V
Q_{rr}	Reverse Recovery Charge	V_{DD} = –12.5V, I_F = –10A, di/dt = 300A/µs		17.4		nC
t_{rr}	Reverse Recovery Time			21		ns

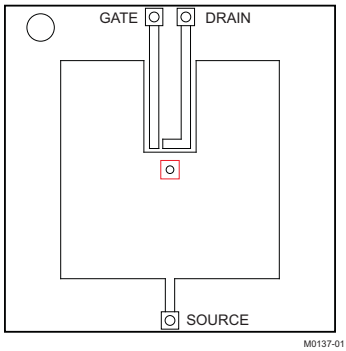
THERMAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

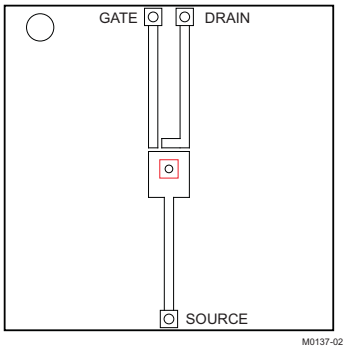
PARAMETER		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case(1) (2)			2.8	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient(1) (2)			57	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1 inch^2 Cu (2 oz.) pad on a 1.5 × 1.5 in 0.060 inch thick FR4 board. $R_{\theta JC}$ is specified by design while $R_{\theta JA}$ is determined by the user's board design.

(2) Device mounted on FR4 Material with 1 inch^2 of Cu (2 oz.).



Max $R_{\theta JA}$ = 57°C/W when mounted on 1inch^2 of 2 oz. Cu.



Max $R_{\theta JA}$ = 158°C/W when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

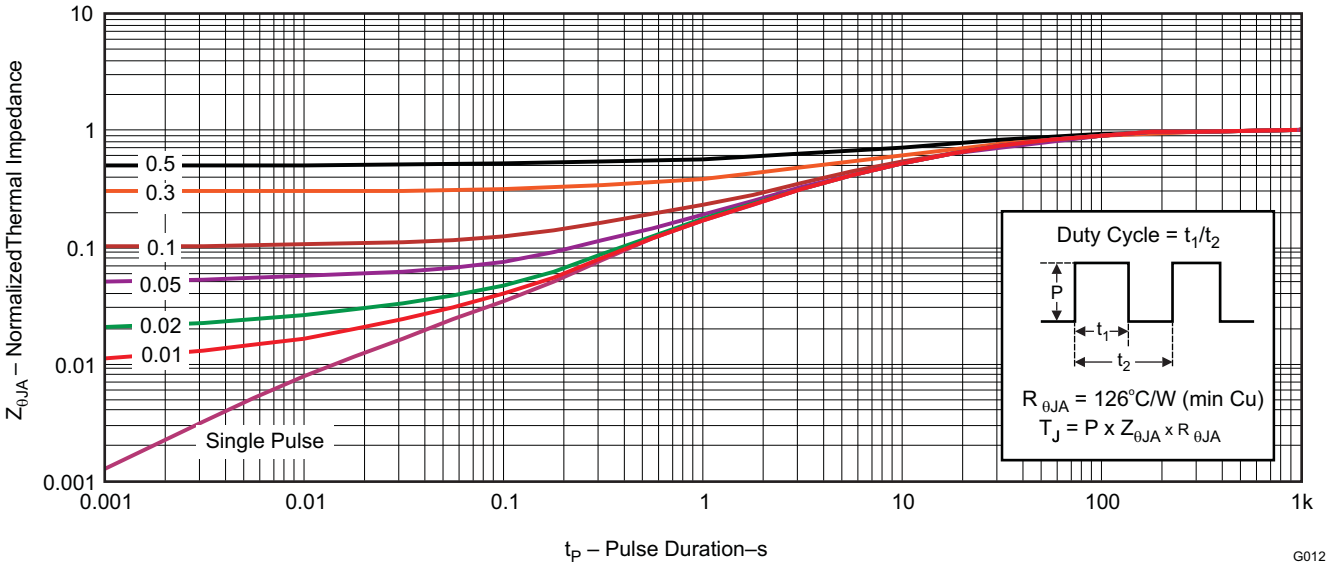


Figure 1. Transient Thermal Impedance

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

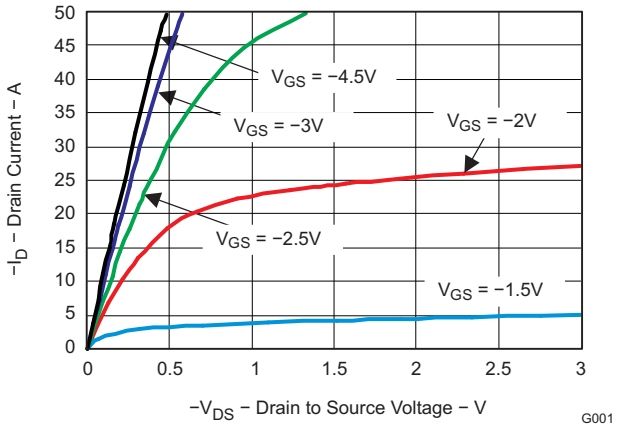


Figure 2. Saturation Characteristics

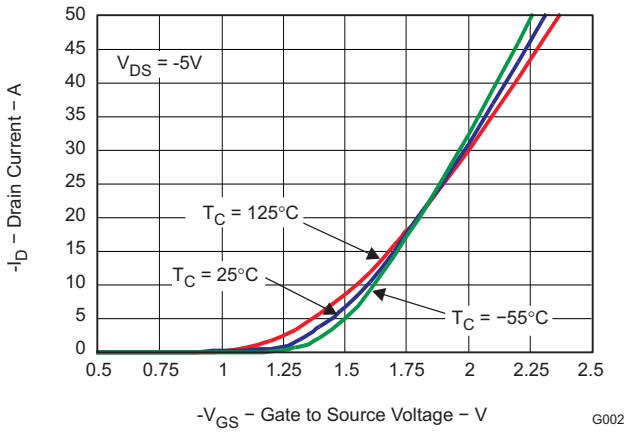


Figure 3. Transfer Characteristics

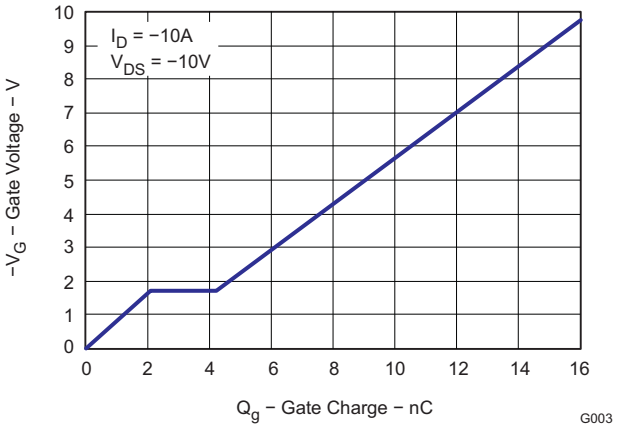


Figure 4. Gate Charge

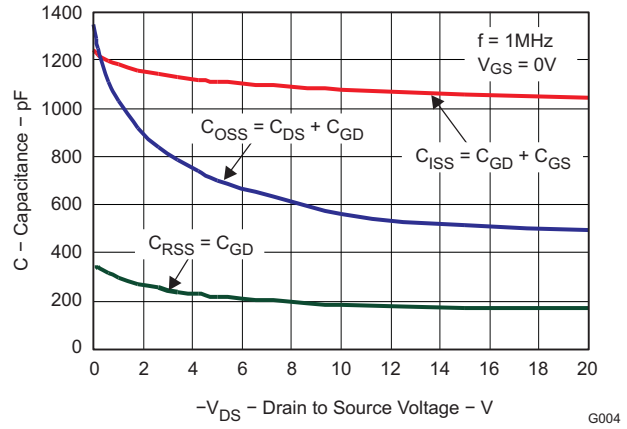


Figure 5. Capacitance

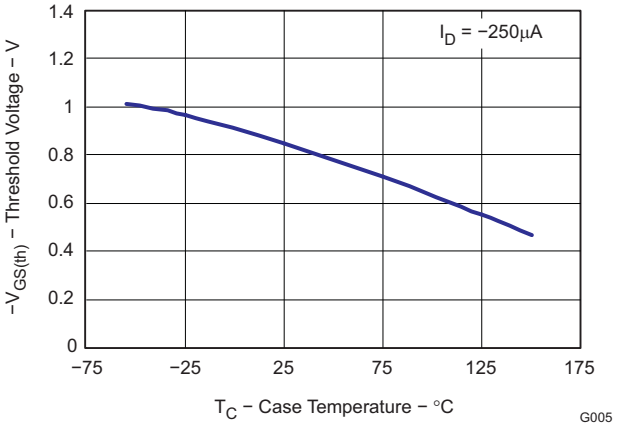


Figure 6. Threshold Voltage vs. Temperature

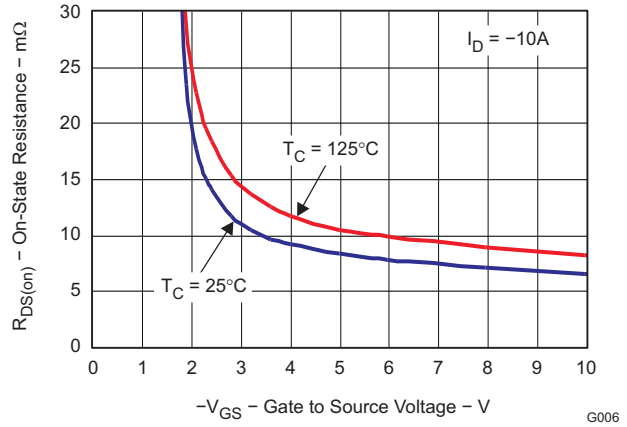


Figure 7. On Resistance vs. Gate Voltage

TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

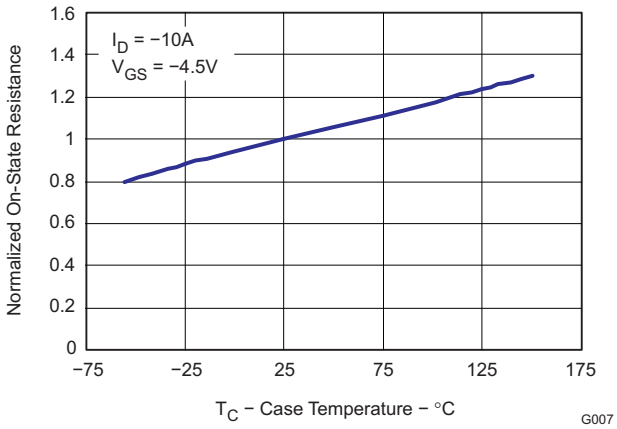


Figure 8. On Resistance vs. Temperature

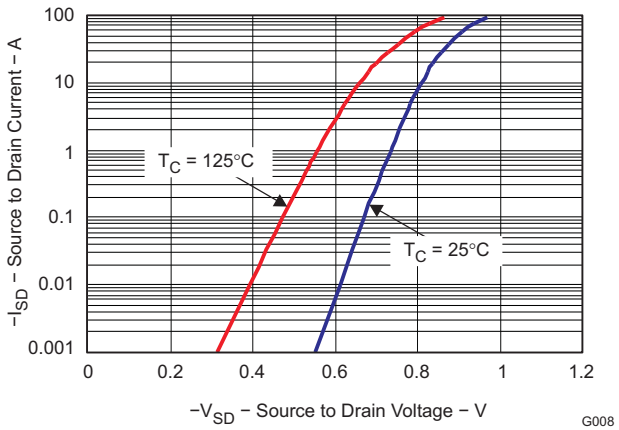


Figure 9. Typical Diode Forward Voltage

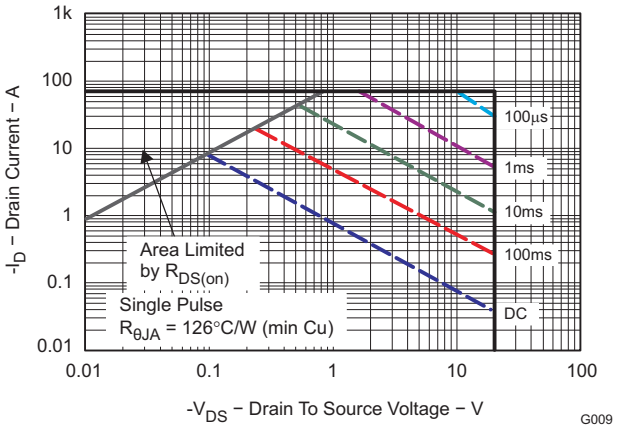


Figure 10. Maximum Safe Operating Area

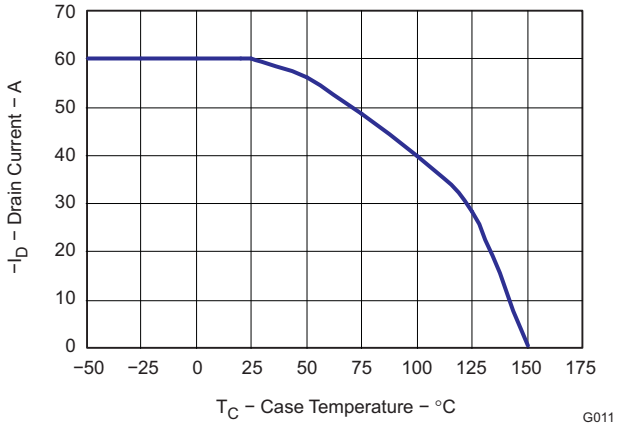
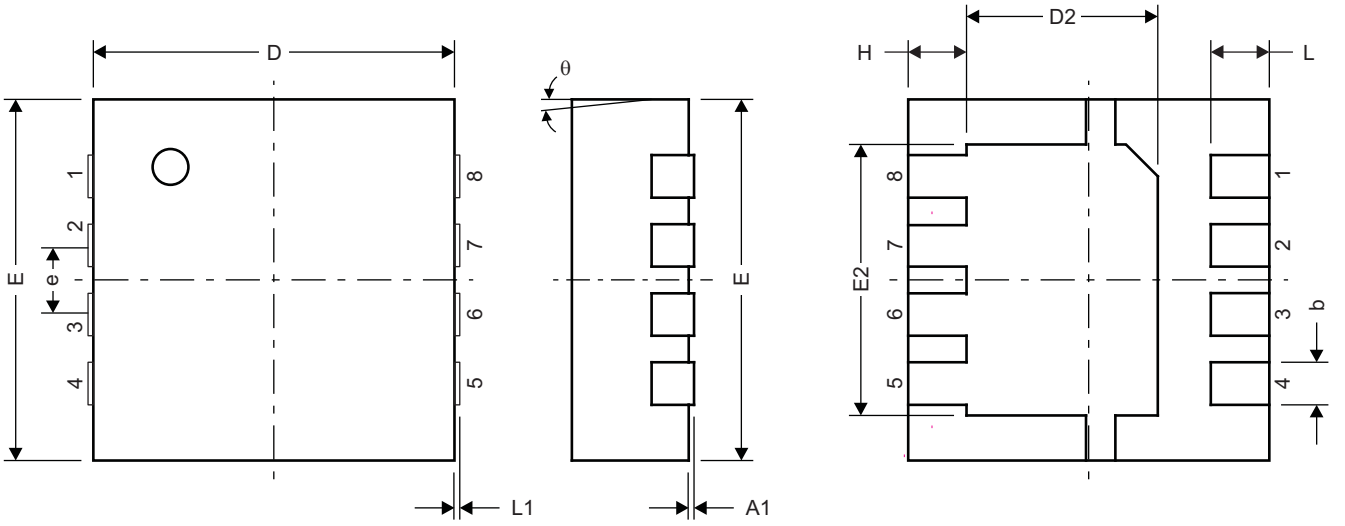


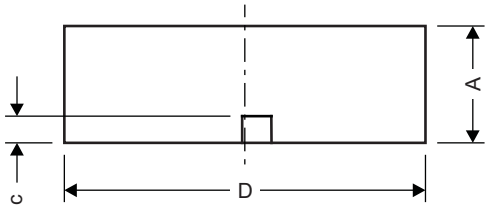
Figure 11. Maximum Drain Current vs. Temperature

MECHANICAL DATA

CSD25401Q3 Package Dimensions



Top View Side View Bottom View



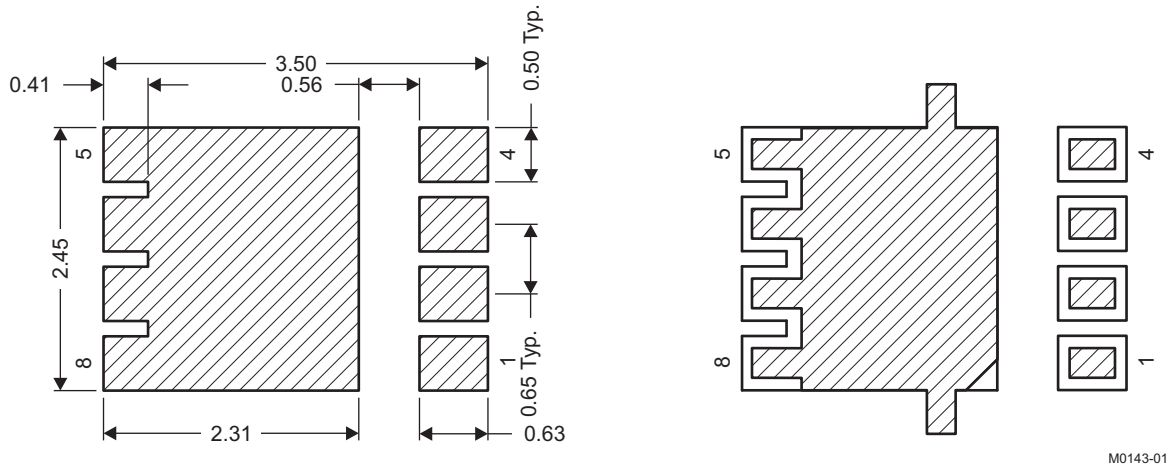
Front View

Pinout	
Drain	1,2,3
Gate	4
Source	5,6,7,8

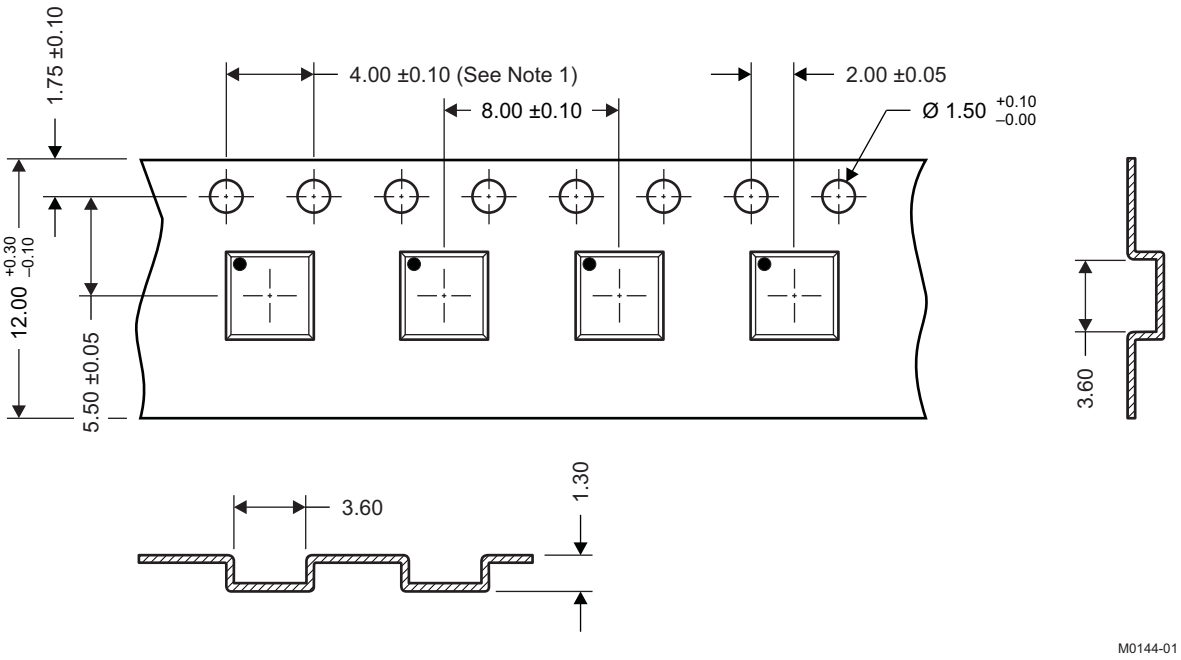
M0142-01

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.950	1.000	1.100	0.037	0.039	0.043
A1	0.000	0.000	0.050	0.000	0.000	0.002
b	0.280	0.340	0.400	0.011	0.013	0.016
c	0.150	0.200	0.250	0.006	0.008	0.010
D	3.200	3.300	3.400	0.126	0.130	0.134
D1	–	–	–	–	–	–
D2	1.650	1.750	1.800	0.065	0.069	0.071
E	3.200	3.300	3.400	0.126	0.130	0.134
E1	–	–	–	–	–	–
E2	2.350	2.450	2.550	0.093	0.096	0.100
e	0.650 TYP			0.026		
H	0.35	0.450	0.550	0.014	0.018	0.022
L	0.35	0.450	0.550	0.014	0.018	0.022
L1	–	–	–	–	–	–
θ	–	–	–	–	–	–

Recommended PCB Pattern



Tape and Reel Information



Notes:

1. 10 sprocket hole pitch cumulative tolerance ±0.2
2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
3. Material:black static dissipative polystyrene
4. All dimensions are in mm (unless otherwise specified)
5. Thickness: 0.30 ±0.05mm
6. MSL1 260°C (IR and Conection) PbF Reflow Compatible

Package Marking Information

Location

1st Line

CSD = Fixed Characters

NNNNN = Product Code

2nd Line (Date Code)

YY = Last 2 digits of the Year

WW = 2-digit Work Week

C = Country of Origin

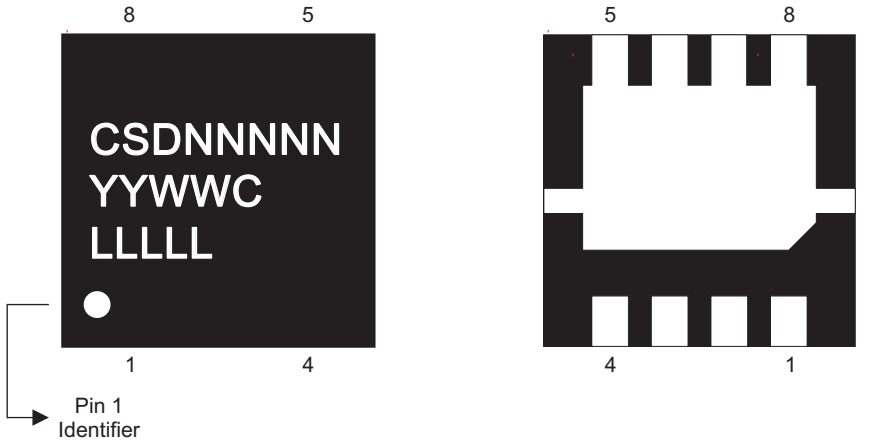
> Philippines = P

> Taiwan = T

> China = C

3rd Line

LLLLL = Last 5 digits of the Wafer Lot #



REVISION HISTORY

Changes from Original (August 2009) to Revision A **Page**

- Changed 300s to 300µs in Note 2 of the Abs Max Ratings table 1
- Changed Q_g Gate Charge Total (4.5V) - max value From: 2.3 To: 12.3 2

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)
CSD25401Q3	ACTIVE	SON	DQG	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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RFID	www.ti-rfid.com	Space, Avionics & Defense	www.ti.com/space-avionics-defense
RF/IF and ZigBee® Solutions	www.ti.com/lprf	Video and Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless-apps

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